

3-9-04

L	Hits	Search Text	DB	Time stamp
Number 1	21	chan-darin-a.in.	USPAT; US-PGPUB; EPO; JPO;	2004/03/09 16:13
2	0	chan-darin-a.in. and second adj transistor	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/09 16:13
3	14	chan-darin-a.in. and transistor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/03/09 16:14
4	1	(chan-darin-a.in. and transistor) and source and drain and (silicon adj layer)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/03/09 16:14
5	7	US-5908309-\$ or US-5015595-\$ or US-5273914-\$ or US-4902634-\$ or US-4422885-\$ or US-4771014-\$ or US-4477310-\$ or US-4773551-\$ or US-6501097-\$ or US-4642878-\$ or US-6501097-\$ or US-6235568-\$ or US-6440832-\$ or US-5963278-\$ or US-5899547-\$ or US-64607748-\$ or US-5627399-\$ or US-6420730-\$ or US-5834350-\$ or US-5428224-\$ or US-5162877-\$ or US-5909400-\$ or US-6180986-\$ or US-6537891-\$).did. or (US-20020195623-\$ or US-20010016377-\$ or US-20020130393-\$ or US-20020102780-\$ or US-20020171077-\$).did.	USPAT; US-PGPUB US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:15 2004/03/09 16:33
7	39	US-6501097-\$ or US-4642878-\$ or US-4637124-\$ or US-6235568-\$ or US-6440832-\$ or US-5963278-\$ or US-5899547-\$ or US-6420730-\$ or US-5627399-\$ or US-5428224-\$ or US-5834350-\$ or US-5428224-\$ or US-5162877-\$ or US-5909400-\$ or US-6180986-\$ or US-6537891-\$).did. or (US-5463238-\$ or US-5164803-\$).did. or (US-20020195623-\$ or US-20010016377-\$ or US-20020130393-\$ or US-20020102780-\$ or US-20020171077-\$).did.) and (second adj transistor) (second adj transistor) and (diffusivity)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/03/09 16:34

8	39	((second adj transistor) and	USPAT;	2004/03/09
		(diffusivity)) not (chan-darin-a.in.	US-PGPUB;	16:34
i		((US-6100124-\$ or US-5937285-\$ or	EPO; JPO;	
		US-5908309-\$ or US-5015595-\$ or	IBM_TDB	
		US-5273914-\$ or US-4902634-\$ or		
		US-4422885-\$ or US-4771014-\$ or		
		US-4477310-\$ or US-4703551-\$ or		
		US-6501097-\$ or US-4642878-\$ or		l i
		US-4637124-\$ or US-6235568-\$ or		
		US-6440832-\$ or US-5963278-\$ or		
		US-5899547-\$ or US-6060748-\$ or		
		US-5627399-\$ or US-6420730-\$ or		
		US-5834350-\$ or US-5428224-\$ or		
		US-5162877-\$ or US-5909400-\$ or		
		US-6180986-\$ or US-6537891-\$).did. or		
		(US-5463238-\$ or US-5164803-\$).did. or		
		(US-20020195623-\$ or US-20010016377-\$ or		
		US-20020130393-\$ or US-20020102780-\$ or		
		US-20020171077-\$).did.))		
9	33	(((second adj transistor) and	USPAT;	2004/03/09
		(diffusivity)) not (chan-darin-a.in.	US-PGPUB;	16:34
		((US-6100124-\$ or US-5937285-\$ or	EPO; JPO;	
		US-5908309-\$ or US-5015595-\$ or	IBM TDB	
		US-5273914-\$ or US-4902634-\$ or		
		US-4422885-\$ or US-4771014-\$ or		
		US-4477310-\$ or US-4703551-\$ or		l i
		US-6501097-\$ or US-4642878-\$ or		
		US-4637124-\$ or US-6235568-\$ or		
		US-6440832-\$ or US-5963278-\$ or		1
		US-5899547-\$ or US-6060748-\$ or		1
		US-5627399-\$ or US-6420730-\$ or		1 .
		US-5834350-\$ or US-5428224-\$ or		1
		US-5162877-\$ or US-5909400-\$ or		
	1	US-6180986-\$ or US-6537891-\$).did. or		
		(US-5463238-\$ or US-5164803-\$).did. or		
		(US-20020195623-\$ or US-20010016377-\$ or		
		US-20020130393-\$ or US-20020102780-\$ or		
		US-20020171077-\$).did.))) and (source and		1
		drain)		
10	17	((((second adj transistor) and	USPAT;	2004/03/09
	1	(diffusivity)) not (chan-darin-a.in.	US-PGPUB;	16:34
	<b>i</b>	((US-6100124-\$ or US-5937285-\$ or	EPO; JPO;	
		US-5908309-\$ or US-5015595-\$ or	IBM_TDB	
		US-5273914-\$ or US-4902634-\$ or	_	i i
		US-4422885-\$ or US-4771014-\$ or		
		US-4477310-\$ or US-4703551-\$ or		
	[	US-6501097-\$ or US-4642878-\$ or		
		US-4637124-\$ or US-6235568-\$ or		
		US-6440832-\$ or US-5963278-\$ or		
		US-5899547-\$ or US-6060748-\$ or		
		US-5627399-\$ or US-6420730-\$ or		
		US-5834350-\$ or US-5428224-\$ or		
1		US-5162877-\$ or US-5909400-\$ or		1
		US-6180986-\$ or US-6537891-\$).did. or		
		(US-5463238-\$ or US-5164803-\$).did. or		
		(US-20020195623-\$ or US-20010016377-\$ or		
	]	US-20020130393-\$ or US-20020102780-\$ or		
		US-20020171077-\$).did.))) and (source and		j l
		drain)) and (silicon adj layer)		
-	5	(("6100124") or ("6153443") or	USPAT;	2003/08/26
		("6235568") or ("5940319") or	US-PGPUB;	11:04
		("5937285")).PN.	EPO; JPO;	
			IBM_TDB	
-	9	("5089441"   "5168072"   "5252501"	USPAT	2003/01/30
		"5397909"   "5403434"   "5716861"		19:19
		"5801078"   "5908309"   "6066523").PN.		1 0000 /00 /00
-	2	("5273914"   "5290712").PN.	USPAT	2003/01/30
1	I		1	19:21

-	13	("4366613"   "4422885"   "4477310"	USPAT	2003/01/30
		"4703551"   "4771014"   "4786609"		19:23
	İ	"4902634"   "4975718"   "4987089"     "5015595"   "5030582"   "5132234"		
		"5141890").PN.		
-	1	"6501097"	USPAT;	2003/01/30
			US-PGPUB; EPO; JPO;	19:50
			IBM_TDB	
-	2	("5403775"   "5872031").PN.	USPAT	2003/01/30
_	6	5937285.URPN.	USPAT	19:58   2003/01/30
				19:59
-	2	("5403775"   "5872031").PN.	USPAT	2003/01/30
_	6	("4530150"   "4562638"   "4590663"	USPAT	20:04
		"4599789"   "4637124"   "4642878").PN.		15:49
-	6	("4366613"   "4488351"   "4505024"	USPAT	2003/01/31
_	58	"4525920"   "4530150"   "4536944").PN. ("NMOS" and "PMOS" and (second adj	USPAT;	15:47
		transistor) and (deep\$4 with (source)))	US-PGPUB;	16:38
			EPO; JPO;	
_	35	(("NMOS" and "PMOS" and (second adj	IBM_TDB USPAT;	2003/01/31
		transistor) and (deep\$4 with (source))))	US-PGPUB;	15:56
	}	and thickness	EPO; JPO;	
_	35	((("NMOS" and "PMOS" and (second adj	IBM_TDB USPAT;	2003/01/31
		transistor) and (deep\$4 with (source))))	US-PGPUB;	15:58
		and thickness) and (diffus\$4 or deplet\$4	EPO; JPO;	
_	33	or dop\$4 or ion\$4)   (((("NMOS" and "PMOS" and (second adj	IBM_TDB   USPAT;	2003/01/31
		transistor) and (deep\$4 with (source))))	US-PGPUB;	15:59
		and thickness) and (diffus\$4 or deplet\$4 or dop\$4 or ion\$4)) and etch\$4	EPO; JPO; IBM TDB	
_	33	((((("NMOS" and "PMOS" and (second adj	USPAT;	2003/01/31
		transistor) and (deep\$4 with (source))))	US-PGPUB;	16:01
		and thickness) and (diffus\$4 or deplet\$4 or dop\$4 or ion\$4)) and etch\$4) and	EPO; JPO; IBM TDB	
		(method or process)	1511_155	
-	10	(((((("NMOS" and "PMOS" and (second adj	USPAT;	2003/01/31
		transistor) and (deep\$4 with (source)))) and thickness) and (diffus\$4 or deplet\$4	US-PGPUB; EPO; JPO;	16:07
		or dop\$4 or ion\$4)) and etch\$4) and	IBM_TDB	
		(method or process)) and (oxidi\$3)	Henna.	2003/01/31
-	0	<pre>((((((("NMOS" and "PMOS" and (second adj transistor) and (deep\$4 with (source))))</pre>	USPAT; US-PGPUB;	16:08
		and thickness) and (diffus\$4 or deplet\$4	EPO; JPO;	
		or dop\$4 or ion\$4)) and etch\$4) and (method or process)) and (oxidi\$3)) not	IBM_TDB	:
		((((("NMOS" and "PMOS" and (second adj		
		transistor) and (deep\$4 with (source))))		
		and thickness) and (diffus\$4 or deplet\$4 or dop\$4 or ion\$4)) and etch\$4) and		
		(method or process))		
-	23	(((((("NMOS" and "PMOS" and (second adj	USPAT;	2003/01/31
		transistor) and (deep\$4 with (source)))) and thickness) and (diffus\$4 or deplet\$4	US-PGPUB; EPO; JPO;	16:08
		or dop\$4 or ion\$4)) and etch\$4) and	IBM_TDB	
		(method or process)) not (((((("NMOS"		
		and "PMOS" and (second adj transistor) and (deep\$4 with (source)))) and		
		thickness) and (diffus\$4 or deplet\$4 or		
		<pre>dop\$4 or ion\$4)) and etch\$4) and (method   or process)) and (oxidi\$3))</pre>		
-	23	(("NMOS" and "PMOS" and (second adj	USPAT;	2003/01/31
		transistor) and (deep\$4 with (source))))	US-PGPUB;	16:39
		not ((("NMOS" and "PMOS" and (second adj transistor) and (deep\$4 with (source))))	EPO; JPO; IBM TDB	
		and thickness)		

-	82	•	609930"	USPAT	2003/01/31
		•	48485"		16:43
			38565"		
		•	984033"		
		·	012228"   051570"		
			84905"		
			.17278"		
1		•	.85535" I		
		·	00846"		
		·	35195" I		
			75972" I		
		The state of the s	94821"		
		· ·	38959"		
		•	67180"		
İ		•	20048"		
		·	53858"		
		•	75238"	İ	
		· · · · · · · · · · · · · · · · · · ·	95353"		
		· ·	06436"		
		"5567959"   "5568288"   "55	80802"		
		•	12799"		
			81759" j		
	1		07772" j		
		"5818076"   "5838508"   "58	49043"		
		"5899547"   "5917221"   "59	33205"		
		"5963278"   "6011277"   "60	13928"		
		"6054734").PN.	•		
-	8		'4609930"	USPAT;	2003/01/31
		•	48485"	US-PGPUB;	16:44
			38565"	EPO; JPO;	
			84033"	IBM_TDB	!
			12228"		
		· · · · · · · · · · · · · · · · ·	51570"		
		•	084905"		
	[		.17278"		
	!		.85535"		
			200846"		
			235195."		
	1		275972"		
			94821"   338959"		
		· ·	367180"		
		•	20048"		ł
			153858"		
			75238"		
			195353"		
			06436"		
	1	• • • • • • • • • • • • • • • • • • • •	80802"		
		"5604368"   "5604380"   "56	· ·		
		•	81759"		
		·	307772"		
	1	"5818076"   "5838508"   "58	349043" İ		
		"5899547"   "5917221"   "59			
		"5963278"   "6011277"   "60			
	1	"6054734").PN.) and (transi	stor and	,	
		"PMOS" and "NMOS")			
-	18084	("NMOS" and "PMOS" )		USPAT;	2003/01/31
				US-PGPUB;	17:38
	1			EPO; JPO;	
				IBM_TDB	0000 (01 (01
-	247	(("NMOS" and "PMOS" )) and	(partial\$4	USPAT;	2003/01/31
1		near3 remov\$4)		US-PGPUB;	17:39
				EPO; JPO;	
		///!!>P/OC!! !!P//OC!! \\	1 /	IBM_TDB	2002/01/21
-	206	((("NMOS" and "PMOS")) and		USPAT;	2003/01/31
		near3 remov\$4)) and (source	and drain)	US-PGPUB;	17:40
				EPO; JPO;	
1	1			IBM TDB	İ

-	191	(((("NMOS" and "PMOS" )) and (partial\$4	USPAT;	2003/01/31
		near3 remov\$4)) and (source and drain))	US-PGPUB;	17:40
		and (insulat\$4 or dielectric)	EPO; JPO;	
			IBM_TDB	
-	191	((((("NMOS" and "PMOS" )) and (partial\$4	USPAT;	2003/01/31
		near3 remov\$4)) and (source and drain))	US-PGPUB;	17:41
		and (insulat\$4 or dielectric)) and	EPO; JPO;	
		(method or process)	IBM TDB	
-	191	(((((("NMOS" and "PMOS" )) and (partial\$4	USPAT;	2003/01/31
		near3 remov\$4)) and (source and drain))	US-PGPUB;	17:42
	ľ	and (insulat\$4 or dielectric)) and	EPO; JPO;	
		(method or process)) and substrate	IBM TDB	
_	190	(((((("NMOS" and "PMOS" )) and	USPAT;	2003/01/31
		(partial\$4 near3 remov\$4)) and (source	US-PGPUB;	17:44
		and drain)) and (insulat\$4 or	EPO; JPO;	
		dielectric)) and (method or process)) and	IBM TDB	
		substrate) and (dop\$4 or depleti\$4 or ion	_	
		or implant\$4 diffus\$5)		
_	172	((((((("NMOS" and "PMOS" )) and	USPAT;	2003/01/31
		(partial\$4 near3 remov\$4)) and (source	US-PGPUB;	17:46
	[	and drain)) and (insulat\$4 or	EPO; JPO;	
		dielectric)) and (method or process)) and	IBM TDB	
		substrate) and (dop\$4 or depleti\$4 or ion	****-***	
1	1	or implant\$4 diffus\$5)) and (doppant or		
1_	18	depletion or implantation or diffusion)	IIGDAT.	2003/01/31
-	18	(((((((("NMOS" and "PMOS" )) and (partial\$4 near3 remov\$4)) and (source	USPAT; US-PGPUB;	17:47
	1		EPO; JPO;	17:47
		and drain)) and (insulat\$4 or		
	1	dielectric)) and (method or process)) and	IBM_TDB	
		substrate) and (dop\$4 or depleti\$4 or ion		
		or implant\$4 diffus\$5)) and (doppant or		
	]	depletion or implantation or diffusion))		
		and ((second adj region) or (second adj		
		portion))		2002/01/21
-	4	("5097314"   "5461253"   "5627399"	USPAT	2003/01/31
		"5754077").PN.		17:52
-	1	6060748.URPN.	USPAT	2003/01/31
				17:54
-	2777	("NMOS" and "PMOS" and (transistor with	USPAT;	2003/02/03
		(partial\$4 (etch\$4 or remov\$4))))	US-PGPUB;	14:50
			EPO; JPO;	
			IBM_TDB	
-	3211	("NMOS" and "PMOS" and (substrate with	USPAT;	2003/02/03
Ĭ		(partial\$4 (etch\$4 or remov\$4))))	US-PGPUB;	14:52
			EPO; JPO;	
			IBM_TDB	
-	581		USPAT;	2003/02/03
1	201	("NMOS" and "PMOS" and ((silicon adj		
1	301	layer) with (partial\$4 (etch\$4 or	US-PGPUB;	14:52
	301	<pre>  ("NMOS" and "PMOS" and ((sillcon ad)   layer) with (partial\$4 (etch\$4 or   remov\$4))))</pre>	US-PGPUB; EPO; JPO;	
		<pre>layer) with (partial\$4 (etch\$4 or remov\$4))))</pre>	US-PGPUB; EPO; JPO; IBM_TDB	14:52
-	3284	<pre>layer) with (partial\$4 (etch\$4 or remov\$4)))) ((("NMOS" and "PMOS" and (substrate with</pre>	US-PGPUB; EPO; JPO;	14:52
~		<pre>layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or</pre>	US-PGPUB; EPO; JPO; IBM_TDB	14:52
-		<pre>layer) with (partial\$4 (etch\$4 or remov\$4)))) ((("NMOS" and "PMOS" and (substrate with</pre>	US-PGPUB; EPO; JPO; IBM_TDB USPAT;	14:52
-		<pre>layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or</pre>	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB;	14:52
-		<pre>layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj</pre>	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	14:52
-		<pre>layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4)))))) and (method or process)</pre>	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	14:52
-	3284	<pre>layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4)))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with</pre>	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB	14:52 2003/02/03 14:54
-	3284	<pre>layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4)))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or</pre>	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT;	14:52 2003/02/03 14:54 2003/02/03
-	3284	layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4)))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	14:52 2003/02/03 14:54 2003/02/03
-	3284	layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4)))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB;	14:52 2003/02/03 14:54 2003/02/03
	3284	layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4)))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4)))))) and (method or process))	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	14:52 2003/02/03 14:54 2003/02/03
-	3284	layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4)))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process)) and (insulat\$4 or dielectric\$4)	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB	14:52 2003/02/03 14:54 2003/02/03 14:55
-	3284	layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4)))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process)) and (insulat\$4 or dielectric\$4) (((("NMOS" and "PMOS" and (substrate	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB  USPAT; US-PGPUB; EPO; JPO; IBM_TDB	14:52 2003/02/03 14:54 2003/02/03 14:55
-	3284	layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4)))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process)) and (insulat\$4 or dielectric\$4) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4)))))	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB  USPAT; US-PGPUB; EPO; JPO; IBM_TDB	14:52 2003/02/03 14:54 2003/02/03 14:55
-	3284	layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4)))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process)) and (insulat\$4 or dielectric\$4) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB  USPAT; US-PGPUB; EPO; JPO; IBM_TDB	14:52 2003/02/03 14:54 2003/02/03 14:55
-	3284	layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4)))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process)) and (insulat\$4 or dielectric\$4) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and (silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB  USPAT; US-PGPUB; EPO; JPO; IBM_TDB	14:52 2003/02/03 14:54 2003/02/03 14:55
-	3284	layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4)))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process)) and (insulat\$4 or dielectric\$4) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process))	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB  USPAT; US-PGPUB; EPO; JPO; IBM_TDB	14:52 2003/02/03 14:54 2003/02/03 14:55
	3284	layer) with (partial\$4 (etch\$4 or remov\$4))))  ((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4)))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process)) and (insulat\$4 or dielectric\$4) (((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and (silicon adj layer) with (partial\$4 (etch\$4 or remov\$4))))	US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB  USPAT; US-PGPUB; EPO; JPO; IBM_TDB	14:52 2003/02/03 14:54 2003/02/03 14:55

			·	
-	92	<pre>(((((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj</pre>	USPAT; US-PGPUB; EPO; JPO;	2003/02/03 14:56
		layer) with (partial\$4 (etch\$4 or remov\$4)))))) and (method or process))	IBM_TDB	
_	80	and (insulat\$4 or dielectric\$4)) and (oxidi\$3)) and (second adj transistor) (((((("NMOS" and "PMOS" and (substrate	USPAT;	2003/02/03
		with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or	US-PGPUB; EPO; JPO; IBM_TDB	14:58
		remov\$4)))))) and (method or process)) and (insulat\$4 or dielectric\$4)) and (oxidi\$3)) and (second adj transistor)) and (source and drain and gate)		
-	15	<pre>(((((((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj</pre>	USPAT; US-PGPUB; EPO; JPO;	2003/02/03 15:13
		layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process)) and (insulat\$4 or dielectric\$4)) and (oxidi\$3)) and (second adj transistor))	IBM_TDB	
		and (source and drain and gate)) and (second adj portion)		2002 (02 (02
_	65	<pre>(((((((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj layer) with (partial\$4 (etch\$4 or</pre>	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/02/03 15:13
		remov\$4)))))) and (method or process)) and (insulat\$4 or dielectric\$4)) and (oxidi\$3)) and (second adj transistor))	_	
		and (source and drain and gate)) not (((((((("NMOS" and "PMOS" and (substrate with (partial\$4 (etch\$4 or remov\$4))))) or (("NMOS" and "PMOS" and ((silicon adj		
		layer) with (partial\$4 (etch\$4 or remov\$4))))) and (method or process)) and (insulat\$4 or dielectric\$4)) and		
		<pre>(oxidi\$3)) and (second adj transistor)) and (source and drain and gate)) and (second adj portion))</pre>		
_	. 1	"20020179957"	USPAT; US-PGPUB; EPO; JPO;	2003/04/30 10:02
-	0	20020179957.URPN.	IBM_TDB USPAT	2003/04/29 17:55
_	8	"5111255"	USPAT; US-PGPUB; EPO; JPO;	2003/04/30 10:02
_	8	("4558337"   "4590502"   "4686550"   "4800415"   "4806997"   "4814836"   "4860068"   "4862228").PN.	IBM_TDB USPAT	2003/04/30 10:03
-	7	5111255.URPN.	USPAT	2003/04/30 10:04
-	3	("4825264"   "5111255"   "5162877").PN.	USPAT	2003/04/30
_	8	"4800415"   "4806997"   "4814836"   "4860068"   "4862228").PN.	USPAT	2003/04/30
_	7	5111255.URPN.	USPAT	2003/04/30
-	523	((semiconductor adj layer) with etch\$4) and (isolation adj region)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05
_	484	(((semiconductor adj layer) with etch\$4) and (isolation adj region)) and (insulat\$4)	USPĀT; US-PGPUB; EPO; JPO;	2003/05/05 01:44
1	L		IBM_TDB	<u></u>

-	66	((((semiconductor adj layer) with etch\$4)	USPAT;	2003/05/05
		and (isolation adj region)) and	US-PGPUB;	01:45
		(insulat\$4)) and (insulati\$4 adj substrate)	EPO; JPO; IBM TDB	
!!	59	(((((semiconductor adj layer) with	USPAT;	2003/05/05
-	33	etch\$4) and (isolation adj region)) and	US-PGPUB;	01:45
		(insulat\$4)) and (insulati\$4 adj	EPO; JPO;	01.10
		substrate)) and transistor	IBM TDB	
_	40	(((((semiconductor adj layer) with	USPAT;	2003/05/05
		etch\$4) and (isolation adj region)) and	US-PGPUB;	01:45
		(insulat\$4)) and (insulati\$4 adj	EPO; JPO;	
		substrate)) and transistor) and oxidiz\$4	IBM_TDB	
-	39	((((((semiconductor adj layer) with	USPAT;	2003/05/05
		etch\$4) and (isolation adj region)) and	US-PGPUB;	01:46
		(insulat\$4)) and (insulati\$4 adj	EPO; JPO;	
		substrate)) and transistor) and oxidiz\$4)	IBM_TDB	
		and (mask)	UCDAM.	2003/05/05
_	0	((((((((semiconductor adj layer) with	USPAT;	2003/05/05
		etch\$4) and (isolation adj region)) and	US-PGPUB; EPO; JPO;	01:47
		<pre>(insulat\$4)) and (insulati\$4 adj substrate)) and transistor) and oxidiz\$4)</pre>	IBM TDB	
		and (mask)) and resist) and antireflect\$4	1011_100	
_	o	((((((((semiconductor adj layer) with	USPAT;	2003/05/05
		etch\$4) and (isolation adj region)) and	US-PGPUB;	01:47
		(insulat\$4)) and (insulati\$4 adj	EPO; JPO;	
		substrate)) and transistor) and oxidiz\$4)	IBM TDB	
		and (mask)) and resist) and (anti adj	_	
		reflect\$4)		
-	29		USPAT;	2003/05/05
		etch\$4) and (isolation adj region)) and	US-PGPUB;	02:02
		(insulat\$4)) and (insulati\$4 adj	EPO; JPO;	
		substrate)) and transistor) and oxidiz\$4)	IBM_TDB	
	1.4	and (mask)) and resist	TICDAM	2003/05/05
-	14	("4314267"   "4609931"   "4612629"     "4672416"   "4830973"   "4939563"	USPAT	01:57
		4672416		01.37
		"5075250"   "5140400"   "5177584"		
		"5412240"   "5434441").PN.		
_	10	(((((((semiconductor adj layer) with	USPAT;	2003/05/05
		etch\$4) and (isolation adj region)) and	US-PGPUB;	02:04
		(insulat\$4)) and (insulati\$4 adj	EPO; JPO;	
		substrate)) and transistor) and oxidiz\$4)	IBM_TDB	
		and (mask)) not (((((((semiconductor		
		adj layer) with etch\$4) and (isolation		
		adj region)) and (insulat\$4)) and		
		(insulati\$4 adj substrate)) and		
		transistor) and oxidiz\$4) and (mask)) and resist)		
_	127	((((semiconductor adj layer) with etch\$4)	USPAT;	2003/05/05
		and (isolation adj region)) and	US-PGPUB;	02:10
		(insulat\$4)) and (lower adj (portion or	EPO; JPO;	
		region or section or area))	IBM_TDB	
_	112	((((semiconductor adj layer) with	USPAT;	2003/05/05
		etch\$4) and (isolation adj region)) and	US-PGPUB;	02:06
		(insulat\$4)) and (lower adj (portion or	EPO; JPO;	
	1	region or section or area))) and	IBM_TDB	
	110	(insulat\$4 adj layer)	HCDAT.	2003/05/05
-	112	((((((semiconductor adj layer) with etch\$4) and (isolation adj region)) and	USPAT; US-PGPUB;	02:06
		(insulat\$4)) and (lower adj (portion or	EPO; JPO;	02.00
		region or section or area))) and	IBM TDB	
		(insulat\$4 adj layer)) and (substrate and		
}		etch\$4)		
-	0		USPAT;	2003/05/05
		etch\$4) and (isolation adj region)) and	US-PGPUB;	02:07
		(insulat\$4)) and (lower adj (portion or	EPO; JPO;	
		region or section or area))) and	IBM_TDB	
		(insulat\$4 adj layer)) and (substrate and		
		etch\$4)) and (mask and resist and		
1	1	oxidez\$4)	I	1

-	26	(((((((semiconductor adj layer) with	USPAT; US-PGPUB;	2003/05/05 02:07
		etch\$4) and (isolation adj region)) and (insulat\$4)) and (lower adj (portion or	EPO; JPO;	02:07
	-	region or section or area))) and	IBM TDB	
		(insulat\$4 adj layer)) and (substrate and	-	
		etch\$4)) and (mask and resist)		
-	21	((((((((semiconductor adj layer) with	USPAT;	2003/05/05 02:07
		etch\$4) and (isolation adj region)) and (insulat\$4)) and (lower adj (portion or	US-PGPUB; EPO; JPO;	02:07
		region or section or area))) and	IBM TDB	
		(insulat\$4 adj layer)) and (substrate and	_	
		etch\$4)) and (mask and resist)) not		
		((((((((semiconductor adj layer) with		
		etch\$4) and (isolation adj region)) and (insulat\$4)) and (insulati\$4 adj		
		substrate)) and transistor) and oxidiz\$4)		
		and (mask))		
-	12	((((semiconductor adj layer) with	USPAT;	2003/05/05
		etch\$4) and (isolation adj region)) and	US-PGPUB;	02:10
		(insulat\$4)) and (insulati\$4 adj	EPO; JPO;	
		substrate)) and (lower adj (portion or region or section or area))	IBM_TDB	
_	11	((((((semiconductor adj layer) with	USPAT;	2003/05/05
		etch\$4) and (isolation adj region)) and	US-PGPUB;	02:11
		(insulat\$4)) and (insulati\$4 adj	EPO; JPO;	
		substrate)) and (lower adj (portion or	IBM_TDB	
		region or section or area))) not ((((((((semiconductor adj layer) with		
		etch\$4) and (isolation adj region)) and		
		(insulat\$4)) and (lower adj (portion or		
		region or section or area))) and		•
		(insulat\$4 adj layer)) and (substrate and etch\$4)) and (mask and resist)) not		
		(((((((semiconductor adj layer) with		
		etch\$4) and (isolation adj region)) and		
		(insulat\$4)) and (insulati\$4 adj		
·		substrate)) and transistor) and oxidiz\$4)		
1_	11	and (mask))) (((((((semiconductor adj layer) with	USPAT;	2003/05/05
	1	etch\$4) and (isolation adj region)) and	US-PGPUB;	02:13
		(insulat\$4)) and (insulati\$4 adj	EPO; JPO;	
		substrate)) and (lower adj (portion or	IBM_TDB	
		region or section or area))) not		
		<pre>((((((((((semiconductor adj layer) with etch\$4) and (isolation adj region)) and</pre>		
		(insulat\$4)) and (lower adj (portion or		
		region or section or area))) and		
		(insulat\$4 adj layer)) and (substrate and		
		etch\$4)) and (mask and resist)) not (((((((semiconductor adj layer) with		
		etch\$4) and (isolation adj region)) and		
		(insulat\$4)) and (insulati\$4 adj		
		substrate)) and transistor) and oxidiz\$4)		
		and (mask))) not (((((((semiconductor		
		adj layer) with etch\$4) and (isolation adj region)) and (insulat\$4)) and		
		(insulati\$4 adj substrate)) and		
		transistor) and oxidiz\$4) and (mask)) and		
		resist) and antireflect\$4)		0000/05/05
-	523	(((semiconductor adj layer) with etch\$4)	USPAT; US-PGPUB;	2003/05/05 02:14
		and (isolation adj region)) and ((semiconductor adj layer) same etch\$4)	EPO; JPO;	02.14
		// surrounded and talor, pame contal	IBM TDB	
-	523	(((semiconductor adj layer) with etch\$4)	USPAT;	2003/05/05
		and (isolation adj region)) and	US-PGPUB;	02:14
		((semiconductor adj layer) with etch\$4)	EPO; JPO; IBM TDB	
L	L	I	TDL TDD	

-	27	<pre>((((((semiconductor adj layer) with etch\$4) and (isolation adj region)) and (insulat\$4)) and (insulati\$4 adj substrate)) not (((((((semiconductor adj</pre>	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05 02:21
		layer) with etch\$4) and (isolation adj region)) and (insulat\$4)) and (insulati\$4 adj substrate)) and transistor) and oxidiz\$4) and (mask))		
-	4	(((semiconductor adj layer) with etch\$4) and (isolation adj region)) and (lower adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05 02:21
-	7	("5623155"   "5729039"   "5973364"   "6191449"   "6288425"   "6348714"   "6414355"   "2002/0048972").PN.	USPĀT	2003/05/05 02:22
-	592	substrate and insulat\$4 and (isolati\$3 adj region) and (second adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05 02:57
-	86	(substrate and insulat\$4 and (isolati\$3 adj region) and (second adj transistor)) and (mask and resist and oxidiz\$4)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05 02:26
-	85	((substrate and insulat\$4 and (isolati\$3 adj region) and (second adj transistor)) and (mask and resist and oxidiz\$4)) and etch\$4	USPĀT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05 02:28
-	80	<pre>(((substrate and insulat\$4 and (isolati\$3 adj region) and (second adj transistor)) and (mask and resist and oxidiz\$4)) and etch\$4) not ((((semiconductor adj layer) with etch\$4) and (isolation adj region)) and (insulat\$4)) and (insulati\$4 adj substrate))</pre>	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05
-	0	20020125512.URPN.	USPAT	2003/05/05
	10	(substrate and insulat\$4 and (isolati\$3 adj region) and (second adj transistor)) and (lower adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05
_	713	("silicon-on-insulator" or "SOI") and (isolat\$4 adj trench)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05 03:01
_	3	"6037632"	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05 10:32
-	7	("4422089"   "5132769"   "5177572"   "5438215"   "5488236"   "5510634"   "5572048").PN.	USPAT	2003/05/05
-	2	6037632.URPN.	USPAT	2003/05/05 10:36
-	0	("535" and (second adj transistor)) and (fully adj depleted adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05
-	0	("535" and (second adj transistor)) and (partially adj depleted adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05
-	123	("535" and (second adj transistor)) and ("NMOS" and "PMOS")	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05
-	11	(("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05

-	11	(("535" and (second adj transistor)) and	USPAT;	2003/05/05
		("NMOS" and "PMOS")) and (mask or resist	US-PGPUB;	10:47
		or photoresist)	EPO; JPO; IBM TDB	
_	486	"535" and (second adj transistor)	USPAT;	2003/05/05
-	400	333 and (second adj transistor)	US-PGPUB;	11:04
			EPO; JPO;	11.04
			IBM TDB	ļ
-	535	((("silicon-on-insulator" or "SOI") and	USPAT;	2003/05/05
		(isolat\$4 adj trench)) and transistor and	US-PGPUB;	11:08
		etch\$4) and insulat\$3	EPO; JPO;	
			IBM TDB	
-	0	((("535" and (second adj transistor)) and	USPAT;	2003/05/05
		("NMOS" and "PMOS")) not ((("535" and	US-PGPUB;	11:15
1		(second adj transistor)) and ("NMOS" and	EPO; JPO;	
1		"PMOS")) and (mask or resisk or	IBM_TDB	
		photoresist))) and (isolati\$4 adj trench)		
-	0	((("535" and (second adj transistor)) and	USPAT;	2003/05/05
		("NMOS" and "PMOS")) not ((("535" and	US-PGPUB;	11:16
		(second adj transistor)) and ("NMOS" and	EPO; JPO;	
		"PMOS")) and (mask or resisk or	IBM_TDB	
		photoresist))) and (isolat\$4 adj trench)	Hanna.	2002/05/05
-	112	(("535" and (second adj transistor)) and	USPAT;	2003/05/05
		("NMOS" and "PMOS")) not ((("535" and	US-PGPUB;	11:51
		(second adj transistor)) and ("NMOS" and	EPO; JPO; IBM TDB	
		"PMOS")) and (mask or resisk or photoresist))	10t1 TDD	
_	0	pnotoresist)    ((("535" and (second adj transistor)) and	USPAT;	2003/05/05
-		("NMOS" and "PMOS")) not ((("535" and	US-PGPUB;	11:17
		(second adj transistor)) and ("NMOS" and	EPO; JPO;	1111
		"PMOS")) and (mask or resisk or	IBM TDB	
		photoresist))) and (isolat\$4 adj trench)		
_	112	((("535" and (second adj transistor)) and	USPAT;	2003/05/05
		("NMOS" and "PMOS")) not ((("535" and	US-PGPUB;	11:17
		(second adj transistor)) and ("NMOS" and	EPO; JPO;	
		"PMOS")) and (mask or resisk or	IBM_TDB	
		photoresist))) and transistor		
-	0	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2003/05/05
		and ("NMOS" and "PMOS")) not ((("535" and	US-PGPUB;	11:18
		(second adj transistor)) and ("NMOS" and	EPO; JPO;	
		"PMOS")) and (mask or resisk or	IBM_TDB	
		<pre>photoresist))) and transistor) and (isolat\$4 adj trench)</pre>		
	0	1	USPAT;	2003/05/05
		and ("NMOS" and "PMOS")) not ((("535" and	US-PGPUB;	11:18
		(second adj transistor)) and ("NMOS" and	EPO; JPO;	
		"PMOS")) and (mask or resisk or	IBM TDB	
		photoresist))) and transistor) and		
		(isolati\$3 adj trench)		
-	0	(((("535" and (second adj transistor))	USPAT;	2003/05/05
		and ("NMOS" and "PMOS")) not ((("535" and	US-PGPUB;	11:18
		(second adj transistor)) and ("NMOS" and	EPO; JPO;	
		"PMOS")) and (mask or resisk or	IBM_TDB	
		photoresist))) and transistor) and		
1		(trench)	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	2002/05/25
-	483	(((("silicon-on-insulator" or "SOI") and	USPAT;	2003/05/05
		(isolat\$4 adj trench)) and transistor and	US-PGPUB;	11:18
		etch\$4) and insulat\$3) and (isolati\$4 adj	EPO; JPO;	
	65	trench)	IBM_TDB USPAT;	2003/05/05
-	%	((((("silicon-on-insulator" or "SOI") and (isolat\$4 adj trench)) and transistor and	US-PGPUB;	11:50
		etch\$4) and insulat\$3) and (isolati\$4 adj	EPO; JPO;	11.00
		trench)) and (("PMOS" and "NMOS") and	IBM TDB	
		(isolat\$4 adj trench))	12100	
_	9	("4090254"   "4276616"   "4677589"	USPAT	2003/05/05
		"4933899"   "5027323"   "5038191"		11:36
	1	"5060194"   "5757693"   "5761114").PN.		
-	19	· ·	USPAT	2003/05/05
				11:39
-	2	("5898196"   "5909400").PN.	USPAT	2003/05/05
	ļ	<u> </u>	<u></u>	11:42

	0	6180986.URPN.	USPAT	2003/05/05
				11:43
-	19	5909400.URPN.	USPAT	2003/05/05
_	112	<pre>(((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not (("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))) and transistor) not ((((("silicon-on-insulator" or "SOI") and (isolat\$4 adj trench)) and transistor and etch\$4) and insulat\$3) and (isolat\$4 adj trench)) and (("PMOS" and "NMOS") and (isolat\$4 adj trench)))</pre>	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05
-	112	((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) not ((("535" and (second adj transistor)) and ("NMOS" and "PMOS")) and (mask or resisk or photoresist))) not ((((("silicon-on-insulator" or "SOI") and (isolat\$4 adj trench)) and transistor and etch\$4) and insulat\$3) and (isolat\$4 adj trench)) and (isolat\$4 adj trench)) and (isolat\$4 adj trench))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/05 12:01
-	20	"5909400"	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05 15:17
_	2	("5898196"   "5909400").PN.	USPAT	2003/05/05
_	2	(("5,909,400") or ("20010045561")).PN.	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/05/05
-	11	"5940691"	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/08/21 15:00
-	19	"5463238"	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/08/21
_	30	"5940691" or "5463238"	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/08/21 15:01
-	7	("3783052"   "4725875"   "4753896"   "4816893"   "4819052"   "5081062"   "5164803").PN.	USPAT	2003/08/21 15:12
_	3	(("5940691") or ("6110765") or ("5463238")).PN.	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/08/26 11:05
_	41	en-william-g.in.	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/11/21 14:38
-	10	pellerin-john-g.in.	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/11/21 14:38
-	110	michael-mark-w.in.	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/11/21 14:39
-	0	mark-michael-w.in.	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/11/21 14:39

				,
-	157	en-william-g.in. pellerin-john-g.in. michael-mark-w.in.	USPAT; US-PGPUB; EPO; JPO;	2003/11/21 14:39
-	100	(en-william-g.in. pellerin-john-g.in. michael-mark-w.in.) and source and drain	IBM_TDB USPAT; US-PGPUB;	2003/11/21 14:39
		·	EPO; JPO; IBM_TDB	
_	98	((en-william-g.in. pellerin-john-g.in. michael-mark-w.in.) and source and drain) and (second transistor)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/11/21
-	5	((en-william-g.in. pellerin-john-g.in. michael-mark-w.in.) and source and drain) and (second adj transistor)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/11/21 14:42
-	10	((en-william-g.in. pellerin-john-g.in. michael-mark-w.in.) and source and drain) and (second adj source)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/11/21   14:42
-	9	michael-mark-w.in.) and source and drain) and (second adj source)) not (((en-william-g.in. pellerin-john-g.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/09 16:13
_	410	michael-mark-w.in.) and source and drain) and (second adj transistor)) (second adj transistor) and (buried adj	USPAT;	2003/11/21
	110	layer)	US-PGPUB; EPO; JPO; IBM TDB	14:44
-	410	((second adj transistor) and (buried adj layer)) not (en-william-g.in. pellerin-john-g.in. michael-mark-w.in.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/21 14:44
-	31	<pre>(((second adj transistor) and (buried adj layer)) not (en-william-g.in. pellerin-john-g.in. michael-mark-w.in.)) and (second adj source)</pre>	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/11/21 14:44
	20	(US-6440832-\$ or US-5963278-\$ or US-5899547-\$ or US-5937285-\$ or US-6100124-\$ or US-5908309-\$ or US-5273914-\$ or US-5015595-\$ or US-4477310-\$ or US-4902634-\$ or US-4703551-\$ or US-4771014-\$ or US-4422885-\$ or US-6501097-\$ or US-4637124-\$ or US-4642878-\$ or US-6235568-\$ or US-6060748-\$ or US-5627399-\$ or US-6420730-\$ or US-5834350-\$ or US-5428224-\$ or US-5162877-\$ or US-5909400-\$ or US-6180986-\$ or US-6537891-\$).did. or (US-5463238-\$ or US-5164803-\$).did. or (US-20020195623-\$ or US-20010016377-\$ or US-20020130393-\$ or US-20020102780-\$ or US-20020171077-\$).did.	USPAT; US-PGPUB	2003/11/21 15:03 2003/11/21 15:19
_	o	"5811855"   "5821769"   "5877046"   "5929476"   "5940691"   "5985683"   "5985728"   "6054345"   "6061268"   "6084259"   "6144072").PN. 6537891.URPN.	USPAT	2003/11/21
_	0	6537891.URPN.	USPAT	15:21 2003/11/21
1	]			15:21